

Chip Specification

General Description:

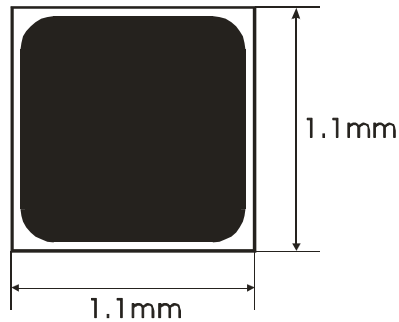
Schottky Diode chips with Mo-barrier for switch mode power rectifiers with the following features:

- * **Guard-ring for stress protection**
- * **Extremely low forward voltage**
- * **125 °C operation junction temperature**
- * **reverse avalanche behavior**

Mechanical Data:

SB 1XX passivated Silicon Chip

| | |
|----------------------|-------------------|
| Demension(mm) | 1.1x 1.1 |
| Thickness: | 350 +- 20 μ m |
| Metallization: | |
| Top (Anode) : | Al Ag |
| Bottom (Cathode) : | TiNiAg |



| | |
|----------------------|---------------|
| Forward Current(A) | 1 A |
| Reverse Voltage (V): | 23, 43, 100 V |

| Type | Chip | VR(V) | VF(V)@25 C at If=1A | IRM@VRMM at 25 C |
|--------|-----------|-------|------------------------|---------------------|
| | size(mm) | | | |
| SB120 | 1.1 X 1.1 | 23 V | 400mV | 0,5mA |
| SB140 | 1.1 X 1.1 | 43 V | 460mV | 0,5mA |
| SB1100 | 1.1 X 1.1 | 100 V | 730mV | 0,5mA |

Note: Other voltages, Vf & Top Metal Al are available

